

L Number	Hits	Search Text	DB	Time stamp
1	286	(GaN or gallium adj nitride) same lateral near10 overgrow\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/10 10:28
2	1	((GaN or gallium adj nitride) same lateral near10 overgrow\$5) and @py<1994	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/10 10:29
3	1	((GaN or gallium adj nitride) same lateral near10 overgrow\$5) and @py<1996	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/10 10:29
4	1	((GaN or gallium adj nitride) same lateral near10 overgrow\$5) and @py<1997	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/10 10:29
5	6	((GaN or gallium adj nitride) same lateral near10 overgrow\$5) and @py<2000	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/10 11:17
6	812	lateral near2 overgrow\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/10 11:17
7	713	epitax\$5 same lateral near2 overgrow\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/10 11:17
9	1	(epitax\$5 same lateral near2 overgrow\$5) same ("iii-v" or gan or gallium adj nitride )and @py<1995	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/10 11:18
8	138	(epitax\$5 same lateral near2 overgrow\$5) and @py<1995	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/10 11:18
10	58	(michael near2 tischler or thomas near2 kuech or robert near2 vaudo).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/10 13:43
11	26	((michael near2 tischler or thomas near2 kuech or robert near2 vaudo).in.) and (gan or gallium near2 nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/10 13:43
12	22	((michael near2 tischler or thomas near2 kuech or robert near2 vaudo).in.) and (gan or gallium near2 nitride)) and remov\$5 near5 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/10 13:49
13	702	(gan or gallium near2 nitride) same remov\$5 near5 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/10 13:49
14	516	(gan or gallium near2 nitride) same remov\$5 near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/10 13:51

15	194	((gan or gallium near2 nitride) near10 (sapphire or "al.2o.sub.3") near4 substrate same remov\$5 near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/10 13:50
16	10	((gan or gallium near2 nitride) near10 (sapphire or "al.2o.sub.3") near4 substrate same remov\$5 near2 substrate) and @py<2000	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/10 13:50
17	68	((gan or gallium near2 nitride) same remov\$5 near2 substrate) and @py<2000	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/10 13:51